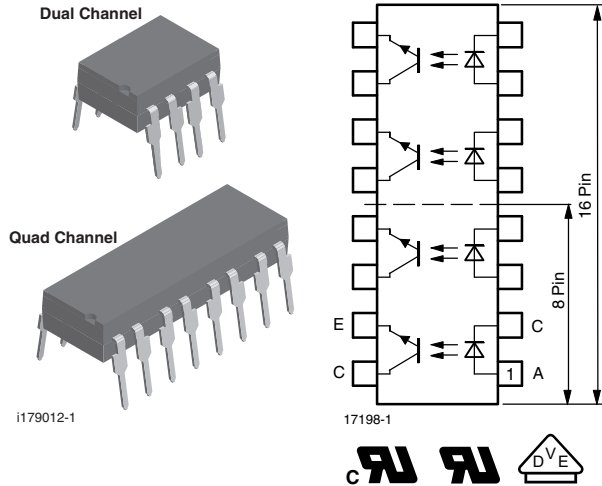


Optocoupler, Phototransistor Output, (Dual, Quad Channel)



FEATURES

- Extra low coupling capacity - typical 0.2 pF
- High common mode rejection
- Low temperature coefficient of CTR
- Rated impulse voltage (transient overvoltage) $V_{IOTM} = 10$ kV peak
- Creepage current resistance according to VDE 0303/IEC 60112 comparative tracking index: $CTI \geq 175$
- Thickness through insulation ≥ 0.4 mm
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



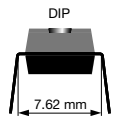
RoHS
COMPLIANT

AGENCY APPROVALS

- UL1577, file no. E52744 system code H, double protection
- CSA 22.2 bulletin 5A, double protection
- DIN EN 60747-5-5 (VDE 0884)
- FIMKO

DESCRIPTION

The TCET2100/TCET4100 consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode, available in 8 pin (dual channel) and 16 pin (quad channel) package.

ORDERING INFORMATION	
<div style="display: flex; justify-content: space-around; align-items: center;"> <div style="border: 1px solid black; padding: 2px 5px; margin: 2px;">T</div> <div style="border: 1px solid black; padding: 2px 5px; margin: 2px;">C</div> <div style="border: 1px solid black; padding: 2px 5px; margin: 2px;">E</div> <div style="border: 1px solid black; padding: 2px 5px; margin: 2px;">T</div> <div style="border: 1px solid black; padding: 2px 5px; margin: 2px;">#</div> <div style="border: 1px solid black; padding: 2px 5px; margin: 2px;">1</div> <div style="border: 1px solid black; padding: 2px 5px; margin: 2px;">0</div> <div style="border: 1px solid black; padding: 2px 5px; margin: 2px;">0</div> </div> <p style="text-align: center; margin-top: 5px;">PART NUMBER</p>	
AGENCY CERTIFIED/PACKAGE	CTR (%)
UL, cUL, VDE	50 to 600
DIP-8, dual channel	TCET2100
DIP-16, quad channel	TCET4100

TCET2100, TCET4100



Vishay Semiconductors Optocoupler, Phototransistor Output,
(Dual, Quad Channel)

ABSOLUTE MAXIMUM RATINGS ⁽¹⁾ ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V_R	6	V
Forward current		I_F	60	mA
Forward surge current	$t_p \leq 10\text{ }\mu\text{s}$	I_{FSM}	1.5	A
Power dissipation		P_{diss}	100	mW
Junction temperature		T_j	125	$^{\circ}\text{C}$
OUTPUT				
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V_{ECO}	7	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10\text{ ms}$	I_{CM}	100	mA
Power dissipation		P_{diss}	150	mW
Junction temperature		T_j	125	$^{\circ}\text{C}$
COUPLER				
Isolation test voltage (RMS)	$t = 1\text{ s}$	V_{ISO}	5300	V_{RMS}
Isolation voltage		V_{IORM}	890	V_P
Total power dissipation		P_{tot}	250	mW
Operating ambient temperature range		T_{amb}	- 55 to + 100	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 55 to + 150	$^{\circ}\text{C}$
Soldering temperature ⁽²⁾	2 mm from case, $t \leq 10\text{ s}$	T_{slid}	260	$^{\circ}\text{C}$

Notes

- (1) Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.
- (2) Refer to wave profile for soldering conditions for through hole devices.

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward voltage	$I_F = \pm 50\text{ mA}$	V_F		1.25	1.6	V
Junction capacitance	$V_R = 0\text{ V}, f = 1\text{ MHz}$	C_j		50		pF
OUTPUT						
Collector emitter voltage	$I_C = 1\text{ mA}$	V_{CEO}	70			V
Emitter collector voltage	$I_E = 100\text{ }\mu\text{A}$	V_{ECO}	7			V
Collector emitter cut-off current	$V_{CE} = 20\text{ V}, I_F = 0, E = 0$	I_{CEO}		10	100	nA
COUPLER						
Collector emitter saturation voltage	$I_F = 10\text{ mA}, I_C = 1\text{ mA}$	V_{CEsat}			0.3	V
Cut-off frequency	$V_{CE} = 5\text{ V}, I_F = 10\text{ mA}, R_L = 100\text{ }\Omega$	f_c		110		kHz
Coupling capacitance	$f = 1\text{ MHz}$	C_k		0.3		pF

Note

- Minimum and maximum values were tested requirements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
I_C/I_F	$V_{CE} = 5\text{ V}, I_F = 5\text{ mA}$	CTR	50		600	%

MAXIMUM SAFETY RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward current		I_F			275	mA
OUTPUT						
Power dissipation		P_{diss}			400	mW
COUPLER						
Rated impulse voltage		V_{IOTM}			10	kV
Safety temperature		T_{si}			175	°C

Note

- According to DIN EN 60747-5-5 (see figure 2). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

INSULATION RATED PARAMETERS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Partial discharge test voltage - routine test	100 %, $t_{test} = 1$ s	V_{pd}	1.669			kV
Partial discharge test voltage - lot test (sample test)	$t_{Tr} = 60$ s, $t_{test} = 10$ s, (see figure 2)	V_{IOTM}	10			kV
		V_{pd}	1.424			kV
Insulation resistance	$V_{IO} = 500$ V	R_{IO}	10^{12}			Ω
	$V_{IO} = 500$ V, $T_{amb} = 100$ °C	R_{IO}	10^{11}			Ω
	$V_{IO} = 500$ V, $T_{amb} = 150$ °C (construction test only)	R_{IO}	10^9			Ω

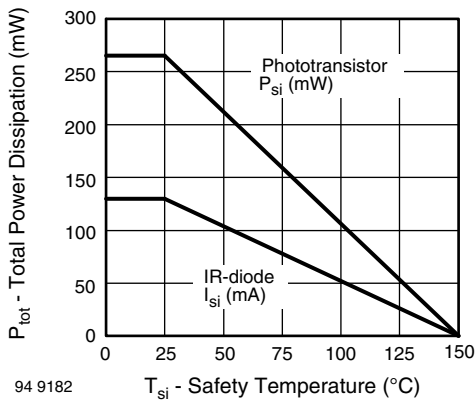


Fig. 1 - Derating Diagram

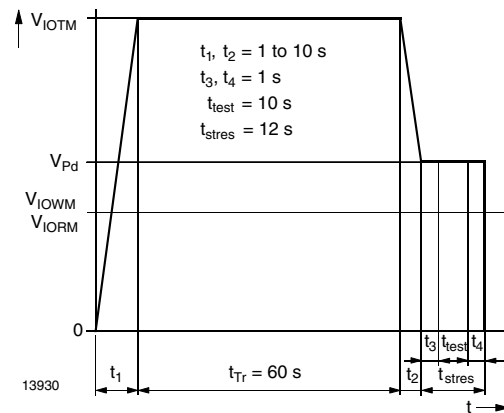
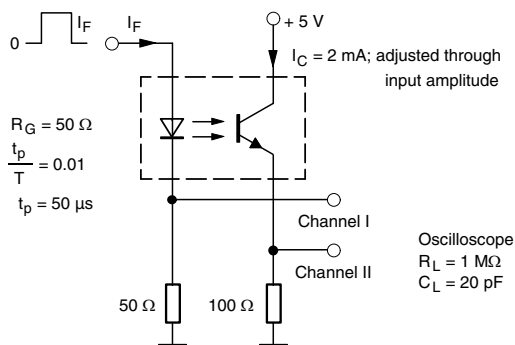


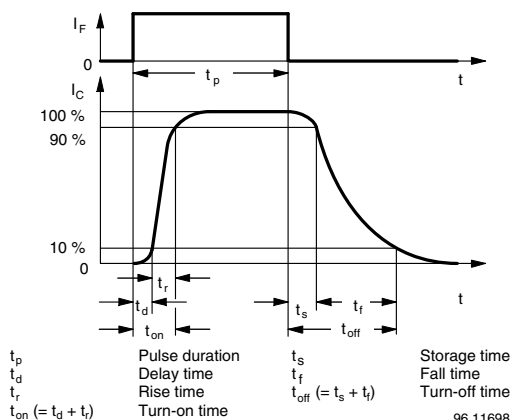
Fig. 2 - Test Pulse Diagram for Sample Test According to DIN EN 60747-5-5/DIN EN 60747-; IEC60747

SWITCHING CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Delay time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_d		3		μs
Rise time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_r		3		μs
Turn-on time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_{on}		6		μs
Storage time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_s		0.3		μs
Fall time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_f		4.7		μs
Turn-off time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_{off}		5		μs
Turn-on time	$V_S = 5\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$, (see figure 4)	t_{on}		9		μs
Turn-off time	$V_S = 5\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$, (see figure 4)	t_{off}		10		μs



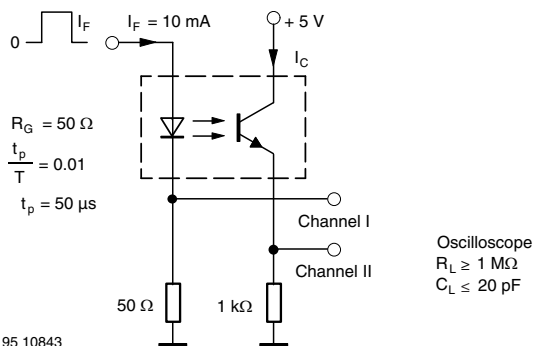
95 10804

Fig. 3 - Test Circuit, Non-Saturated Operation



96 11698

Fig. 5 - Switching Times



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Fig. 4 - Test Circuit, Saturated Operation

TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

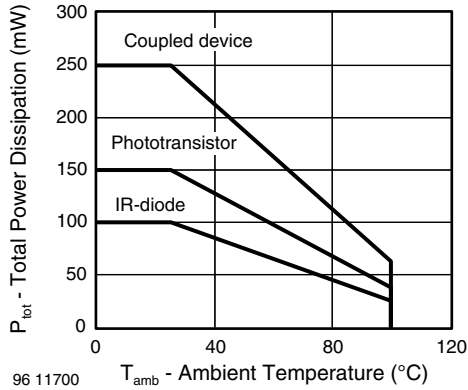


Fig. 6 - Total Power Dissipation vs. Ambient Temperature

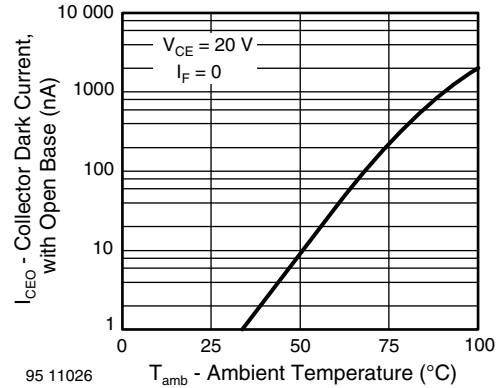


Fig. 9 - Collector Dark Current vs. Ambient Temperature

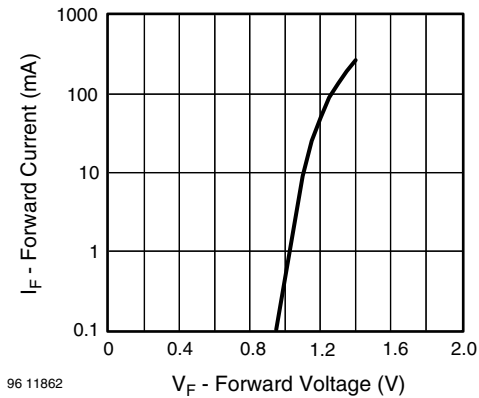


Fig. 7 - Forward Current vs. Forward Voltage

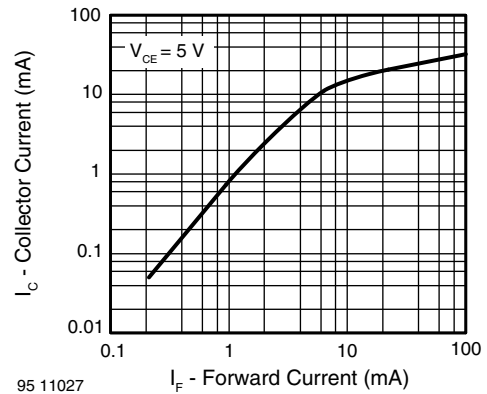


Fig. 10 - Collector Current vs. Forward Current

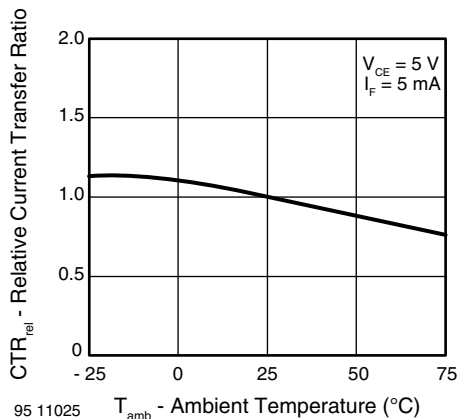


Fig. 8 - Relative Current Transfer Ratio vs. Ambient Temperature

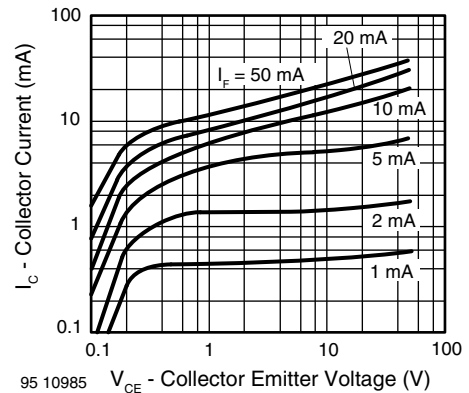
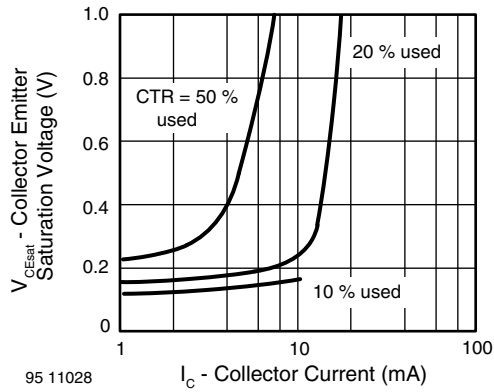


Fig. 11 - Collector Current vs. Collector Emitter Voltage

TCET2100, TCET4100

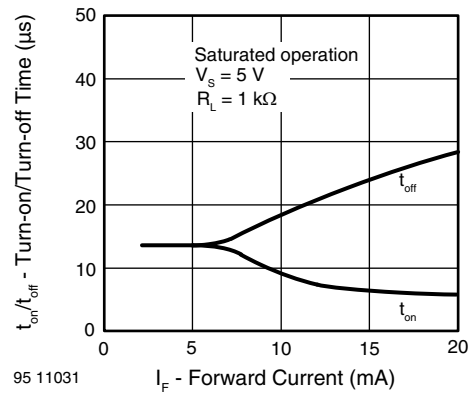


Vishay Semiconductors Optocoupler, Phototransistor Output,
(Dual, Quad Channel)



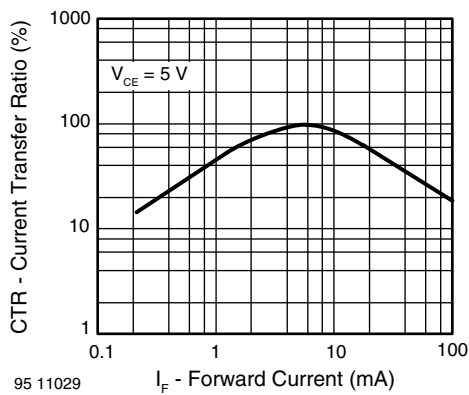
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Fig. 12 - Collector Emitter Saturation Voltage vs. Collector Current



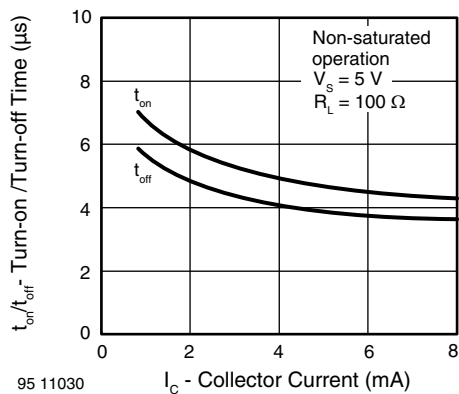
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Fig. 15 - Turn-on/off Time vs. Forward Current



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Fig. 13 - Current Transfer Ratio vs. Forward Current



95 11030

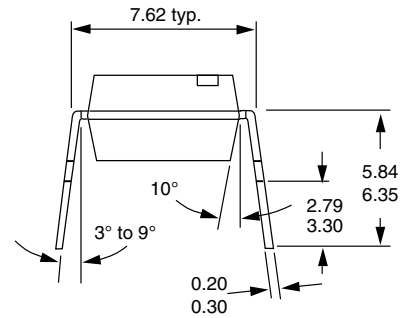
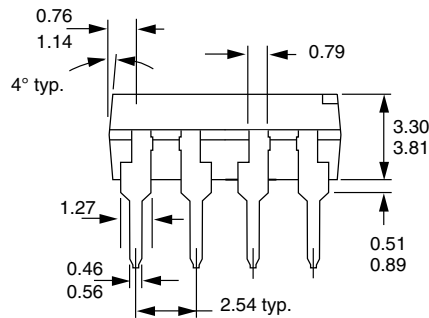
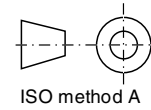
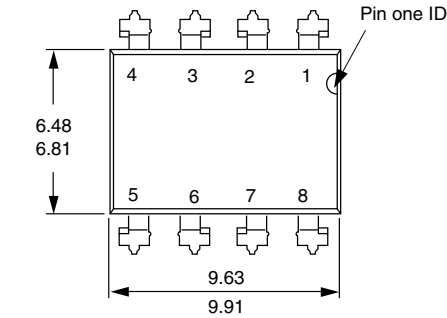
Fig. 14 - Turn-on/off Time vs. Collector Current



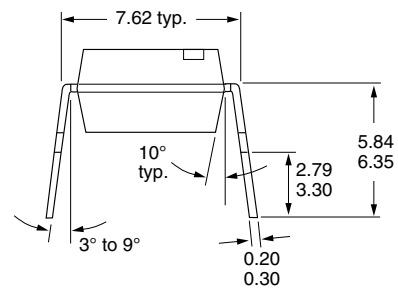
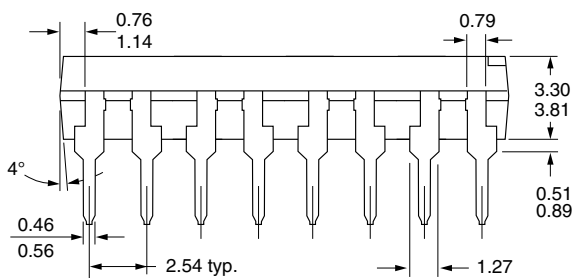
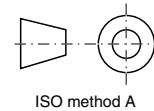
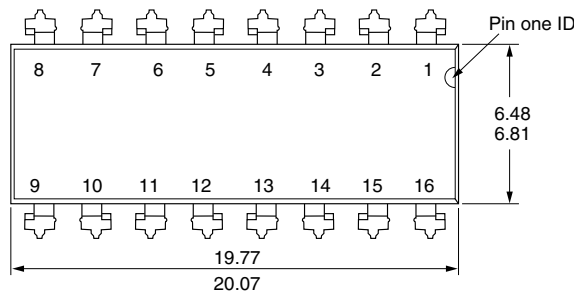
TCET2100, TCET4100

Optocoupler, Phototransistor Output, Vishay Semiconductors
(Dual, Quad Channel)

PACKAGE DIMENSIONS in millimeters

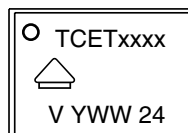


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PACKAGE MARKING



21764-89



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- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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JONHON

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(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели, кабельные сборки и микроволновые компоненты:

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